

Hui Xiong

List of Publications by Year in descending order

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1307594

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17
docs citations

17
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215
citing authors

#	ARTICLE	IF	CITATIONS
1	Controlled synthesis of ZnO hollow microspheres via precursor-template method and its gas sensing property. Applied Surface Science, 2012, 258, 8431-8438.	6.1	49
2	The Advantages of AlGaIn-Based UV-LEDs Inserted With a p-AlGaIn Layer Between the EBL and Active Region. IEEE Photonics Journal, 2013, 5, 1600310-1600310.	2.0	29
3	Temperature Insensitive Optical Fiber Laser Bend Sensor With a Low Detection Limit. IEEE Photonics Technology Letters, 2015, 27, 2599-2602.	2.5	14
4	Effect of the Al _{0.3} Ga _{0.7} As interlayer thickness upon the quality of GaAs on a Ge substrate grown by metal-organic chemical vapor deposition. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2013, 31, 041202.	1.2	9
5	Luminescence and structure regulation of graphitic carbon nitride by electron rich P ions doping. Journal of Luminescence, 2020, 228, 117616.	3.1	9
6	A phosphorus-doped g-C ₃ N ₄ nanosheets as an efficient and sensitive fluorescent probe for Fe ³⁺ detection. Optical Materials, 2021, 119, 111393.	3.6	9
7	Ru ⁴⁺ -assisted phase transition in VO ₂ nanoparticles: Electronic structures and optical properties. Vacuum, 2021, 192, 110495.	3.5	9
8	Fabrication of low-density GaN/AlN quantum dots via GaN thermal decomposition in MOCVD. Nanoscale Research Letters, 2014, 9, 341.	5.7	8
9	First-principles study on stability, electronic and optical properties of Janus-functionalized ZnO monolayer and bilayer for optoelectronic device. Vacuum, 2020, 181, 109749.	3.5	6
10	Effects of polarization on intersubband transitions of Al _x Ga _{1-x} N/GaN multi-quantum wells. Chinese Physics B, 2013, 22, 057302.	1.4	4
11	Low temperature sintering and nonlinear dielectric properties of lithium-doped Ba _{0.6} Sr _{0.4} TiO ₃ thick films prepared by tape-casting. Journal of Materials Science: Materials in Electronics, 2019, 30, 3488-3494.	2.2	4
12	Occurrence and elimination of in-plane misoriented crystals in AlN epilayers on sapphire via pre-treatment control. Chinese Physics B, 2014, 23, 028101.	1.4	3
13	Extraction of Backscattering and Absorption Coefficients of Magnetite Nanosphere Composites from Light-Scattering Measurements: Implications for Optomagnetic Sensing. ACS Applied Nano Materials, 2020, 3, 11172-11183.	5.0	3
14	The design of back surface field layer for a single GaAs solar cell. Proceedings of SPIE, 2009, , .	0.8	1
15	Effects of the V/III Ratio of a Low-Temperature GaN Buffer Layer on the Structural and Optical Properties of Al _x Ga _{1-x} N/GaN Films Grown on AlN-Plane Sapphire Substrates by MOCVD. Chinese Physics Letters, 2012, 29, 088101.	3.3	1
16	Improved Performance of GaN-Based Light-Emitting Diodes via AlInGaIn/InGaIn Electron-Emitting Layer. Applied Physics Express, 2012, 5, 112101.	2.4	1
17	Growth and properties of ZnO film grown on AlN buffer layer by PLD. , 2012, , .		1